APPENDIX

Please amend claim 1 as follows:

1. (Amended) A method comprising:

forming a metal oxide semiconductor radio frequency circuit element over a triple well in a substrate; and

biasing a well of said triple well through a resistor.

Please cancel claim 6 without prejudice.

Please amend claim 20 as follows:

20. (Amended) A method comprising:

forming a first metal oxide semiconductor radio frequency circuit element over a triple well in a substrate;

biasing a first well of said triple well through a first resistor with a first bias potential;

forming a second metal oxide semiconductor radio frequency circuit element over a second triple well in a substrate; and

biasing a second well of said second triple well through a second resistor coupled to said first bias potential.

Please cancel claim 25.

Please amend claim 26 as follows:

26. (Amended) The method of claim [25] 20 including biasing said wells through resistors having a resistance greater than 100 ohms.

Please add the following new claims 30 *et seq.*:

31. (New) A method comprising:

forming a metal oxide semiconductor circuit element over a triple well in a substrate;

operating said circuit element at a radio frequency; and

biasing a well of said triple well through a resistor which acts as a high impedance relative to a junction capacitance within the triple well.

In view of the remarks, the application is now in condition for allowance and the Examiner's prompt action in accordance therewith is respectfully requested.

Respectfully submitted,

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32. (New) The method of claim 31 including forming an integrated inductor over said triple well.

33. (New) The method of claim 31 including forming a P-type well in an N-well formed in said substrate.

34. (New) The method of claim 33 including biasing the N-type and P-type wells through different resistors.

35. (New) A method of claim 31 including providing a common bias potential to different wells through separate resistors for each well.

36. (New) The method of claim 35 including biasing said wells through resistors having a resistance greater than 100 ohms.

37. (New) The method of claim 31 including coupling a resistor to an N-well within said triple well on a P-type substrate so that said resistor acts as a high impedance relative to the junction capacitance of the N-well to the P-well of the triple well.